

2MBI200N-060-03

IGBT Module

600V / 200A 2 in one-package

■ Features

- VCE(sat) classified for easy parallel connection
- High speed switching
- Voltage drive
- Low inductance module structure

■ Applications

- Inverter for Motor drive
- AC and DC Servo drive amplifier
- Uninterruptible power supply
- Industrial machines, such as Welding machines

■ Maximum ratings and characteristics

● Absolute maximum ratings (at Tc=25°C unless otherwise specified)

Item		Symbol	Rating	Unit
Collector-Emitter voltage		V _{CE} S	600	V
Gate-Emitter voltage		V _{GE} S	±20	V
Collector current	Continuous	I _C	200	A
	1ms	I _C pulse	400	A
		-I _C	200	A
	1ms	-I _C pulse	400	A
Max. power dissipation		P _C	780	W
Operating temperature		T _j	+150	°C
Storage temperature		T _{stg}	-40 to +125	°C
Isolation voltage		V _{is}	AC 2500 (1min.)	V
Screw torque		Mounting *1	3.5	N·m
		Terminals *1	3.5	N·m

*1 : Recommendable value : 2.5 to 3.5 N·m(M5)

● Electrical characteristics (at T_J=25°C unless otherwise specified)

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Zero gate voltage collector current	I _{CE} S	—	—	2.0	V _{GE} =0V, V _{CE} =600V	mA
Gate-Emitter leakage current	I _{GES}	—	—	30	V _{CE} =0V, V _{GE} =±20V	μA
Gate-Emitter threshold voltage	V _{GE(th)}	4.5	—	7.5	V _{CE} =20V, I _C =200mA	V
Collector-Emitter saturation voltage	V _{CE(sat)}	—	—	2.8	V _{GE} =15V, I _C =200A	V
Input capacitance	C _{ies}	—	13200	—	V _{GE} =0V	pF
Output capacitance	C _{oes}	—	2930	—	V _{CE} =10V	
Reverse transfer capacitance	C _{res}	—	1330	—	f=1MHz	
Turn-on time	t _{on}	—	0.6	1.2	V _{CC} =300V	μs
	t _r	—	0.2	0.6	I _C =200A	
Turn-off time	t _{off}	—	0.6	1.0	V _{GE} =±15V	
	t _f	—	0.2	0.35	R _G =9.1ohm	
Diode forward on voltage	V _F	—	—	3.0	I _F =200A, V _{GE} =0V	V
Reverse recovery time	t _{rr}	—	—	0.3	I _F =200A	μs

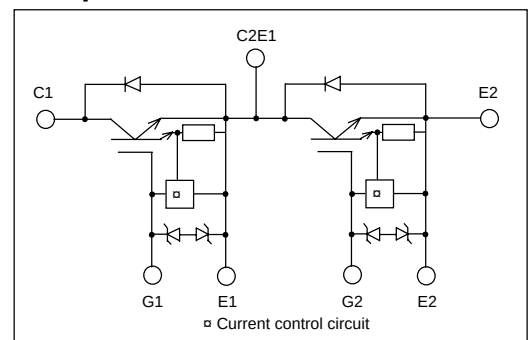
● Thermal resistance characteristics

Item	Symbol	Characteristics			Conditions	Unit
		Min.	Typ.	Max.		
Thermal resistance	R _{th(j-c)}	—	—	0.16	IGBT	°C/W
	R _{th(j-c)}	—	—	0.35	Diode	°C/W
	R _{th(c-f)*2}	—	0.025	—	the base to cooling fin	°C/W

*2 : This is the value which is defined mounting on the additional cooling fin with thermal compound



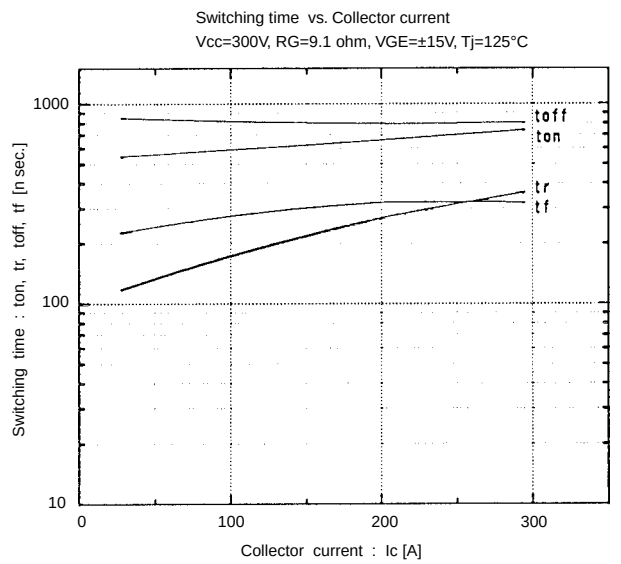
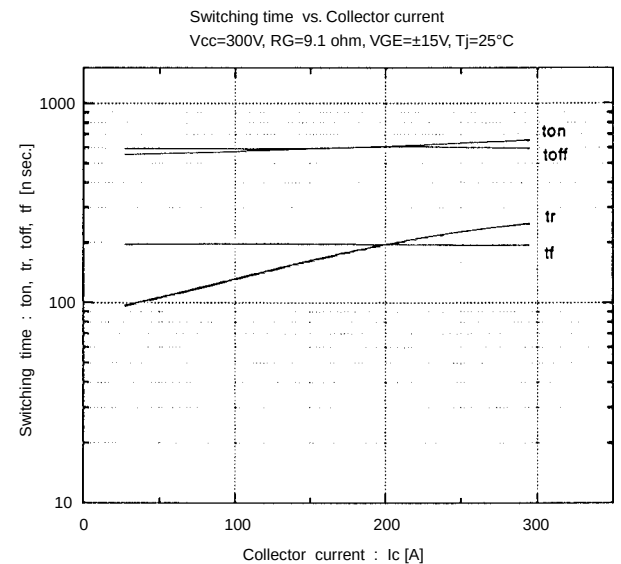
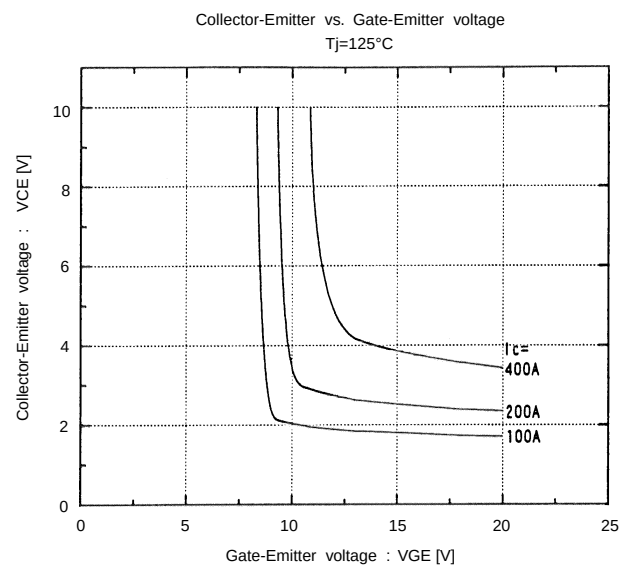
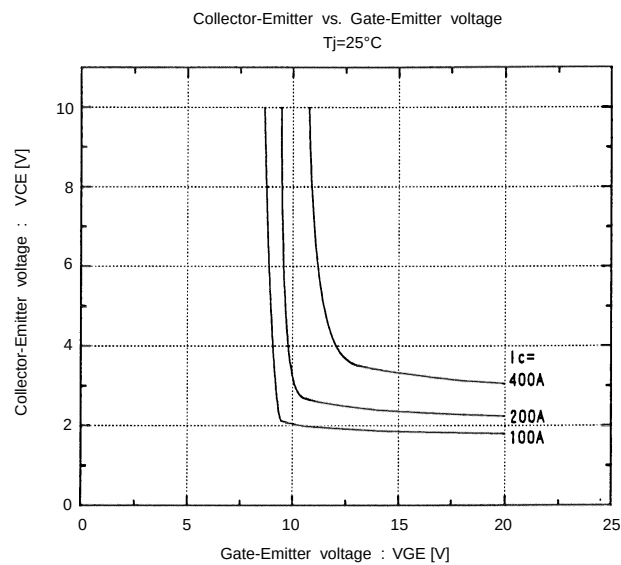
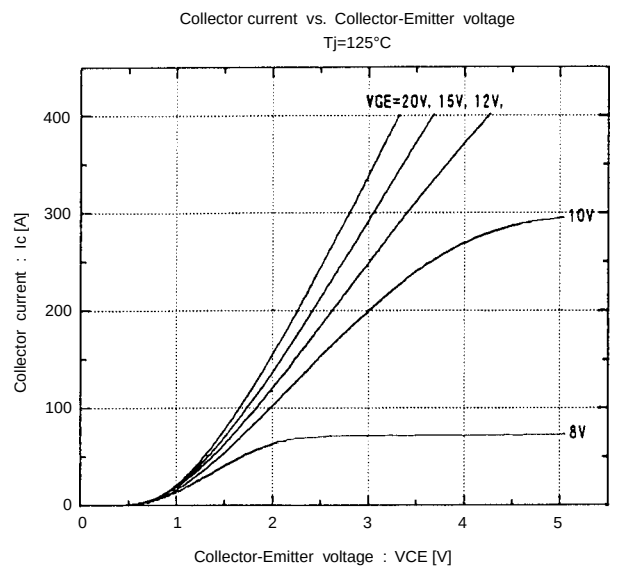
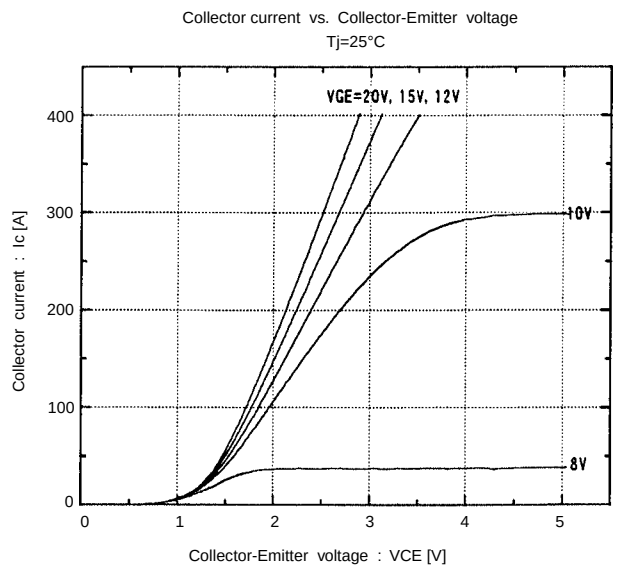
■ Equivalent Circuit Schematic



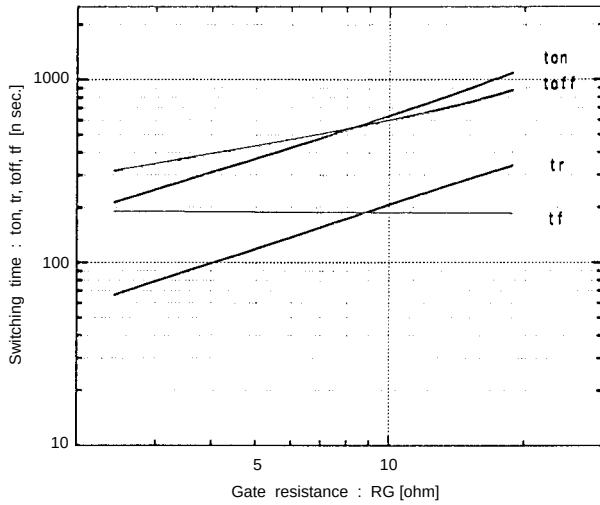
● VCE(sat) classification

Rank	Length	Conditions
F	1.85 to 2.10V	I _C = 200A V _{GE} = 15V T _J = 25°C
A	2.00 to 2.25V	
B	2.15 to 2.40V	
C	2.30 to 2.60V	
D	2.50 to 2.80V	

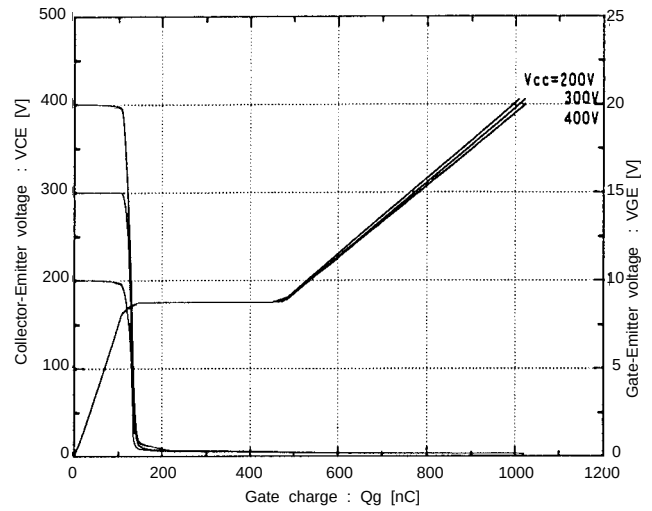
Characteristics (Representative)



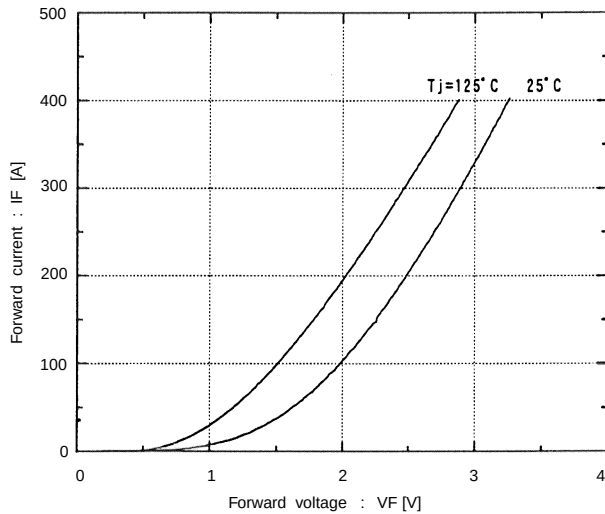
Switching time vs. R_G
 $V_{CC}=300V$, $I_C=200A$, $V_{GE}=\pm 15V$, $T_J=25^\circ C$



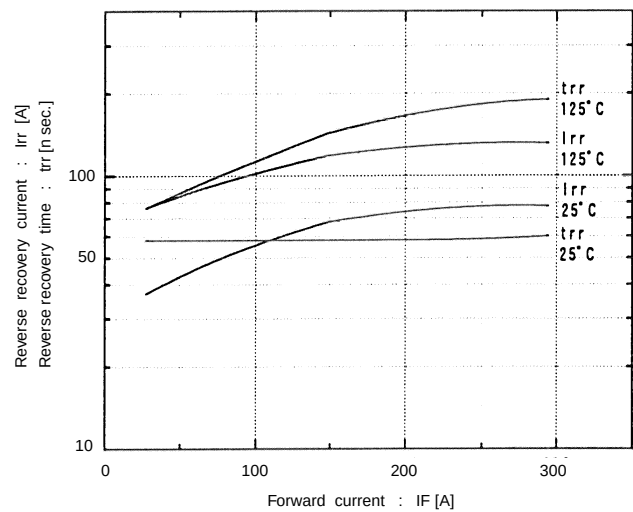
Dynamic input characteristics
 $T_J=25^\circ C$



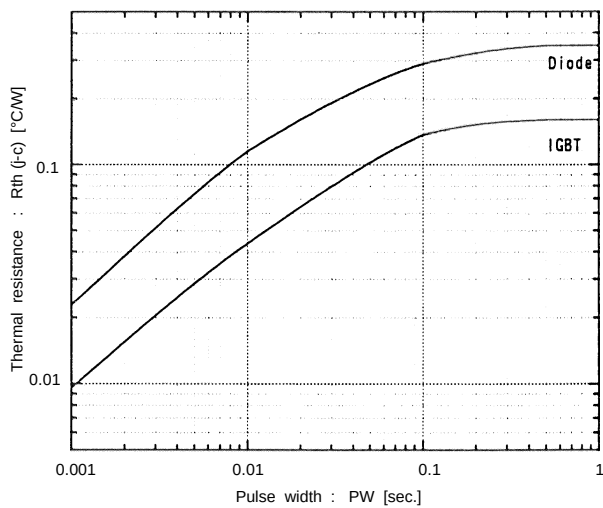
Forward current vs. Forward voltage
 $V_{GE}=0V$



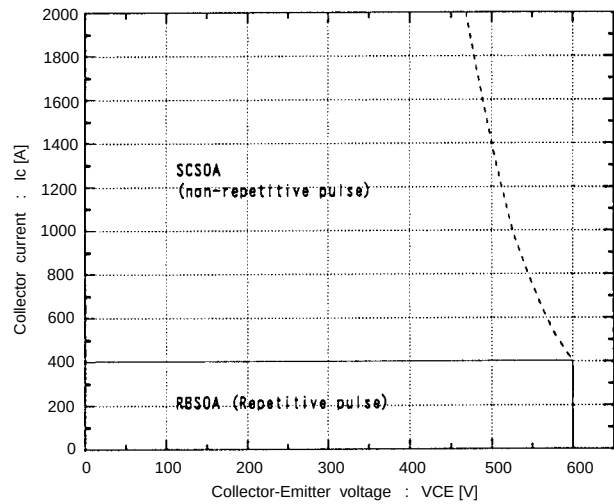
Reverse recovery characteristics
 t_{rr} , I_{rr} , vs. I_F

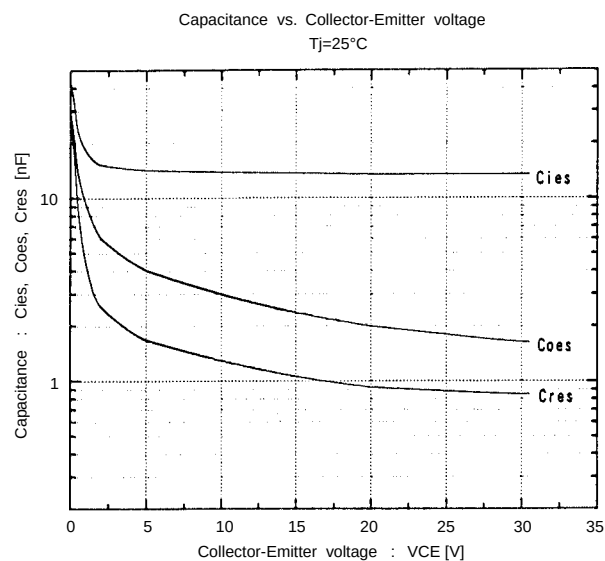


Transient thermal resistance



Reversed biased safe operating area
 $+V_{GE}=15V$, $-V_{GE}\leq 15V$, $T_J\leq 125^\circ C$, $R_G\geq 9.1\text{ ohm}$





Technical drawing of the AMP 110 connector, showing top and side views with dimensions.

Top View Dimensions:

- Overall width: 40 ± 0.6
- Pin pitch (between C2E1 and E2): 23 ± 0.6
- Pin pitch (between E2 and C1): 23 ± 0.6
- Overall height: 45 ± 1
- Pin diameter: 2 ± 0.05
- Pin length: 3 ± 0.05 (Depth 10 min)
- Pin positions: C2E1, E2, C1, G2, E2, G1, E1, G1
- Pin spacing (between G2 and E2): 5 ± 0.6
- Pin spacing (between E2 and G1): 25 ± 0.6
- Pin spacing (between G1 and E1): 5 ± 0.6
- Pin spacing (between E1 and G1): 80 ± 0.3
- Pin spacing (between G1 and E1): 92 ± 1

Side View Dimensions:

- Overall height: 30 ± 1
- Pin height: 6 ± 1
- Pin terminal height: 8 ± 0.5
- Pin terminal width: 22 ± 1

Labels:

- Tab terminal (AMP No. 110)

Mass : 240g

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.